

Title (en)

SELF-ORGANIZED PIN-TYPE NANOSTRUCTURES, AND PRODUCTION THEREOF ON SILICON

Title (de)

SELBSTORGANISIERTE NADELARTIGE NANO-STRUKTUREN UND IHRE HERSTELLUNG AUF SILIZIUM

Title (fr)

NANOSTRUCTURES EN AIGUILLES AUTO-ORGANISEES ET LEUR PRODUCTION SUR DU SILICIUM

Publication

EP 1935010 A2 20080625 (DE)

Application

EP 06807129 A 20061010

Priority

- EP 2006067248 W 20061010
- DE 102005048366 A 20051010

Abstract (en)

[origin: WO2007042520A2] According to the invention, a self-organized pin-type structure (4, 4a) that has no crystal defects, a great aspect ratio, and nano dimensions is produced on the surface of silicon wafers with the aid of an RIE etching process for silicon (3) by selecting the gas concentration of the etching plasma, without taking any additional structuring measure (e-beam, interference lithography, or others), thus obtaining broadband antireflection that can be used in many different ways.

IPC 8 full level

H01L 21/3065 (2006.01); **H01L 21/308** (2006.01); **H01L 31/0216** (2006.01); **H01L 31/18** (2006.01)

CPC (source: EP US)

H01L 21/3065 (2013.01 - EP US); **H01L 21/3086** (2013.01 - EP US); **H01L 21/32137** (2013.01 - EP US); **H01L 21/32139** (2013.01 - EP US)

Citation (search report)

See references of WO 2007042520A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

DE 102005048366 A1 20070419; EP 1935010 A2 20080625; US 2011127641 A1 20110602; US 8058086 B2 20111115; WO 2007042520 A2 20070419; WO 2007042520 A3 20070607

DOCDB simple family (application)

DE 102005048366 A 20051010; EP 06807129 A 20061010; EP 2006067248 W 20061010; US 8972406 A 20061010